Dual Inverter with Open Drain Outputs

The NL27WZ06 is a high performance dual inverter with open drain outputs operating from a $1.65\,\mathrm{V}$ to $5.5\,\mathrm{V}$ supply.

The internal circuit is composed of multiple stages, including an open drain output which provides the capability to set output switching level. This allows the NL27WZ06 to be used to interface $5.0\,\mathrm{V}$ circuits to circuits of any voltage between V_{CC} and $7.0\,\mathrm{V}$ using an external resistor and power supply.

- Extremely High Speed: t_{PD} 2.4 ns (typical) at $V_{CC} = 5.0 \text{ V}$
- Designed for 1.65 V to 5.5 V V_{CC} Operation
- Over Voltage Tolerant Inputs
- \bullet LVTTL Compatible Interface Capability With 5.0 V TTL Logic with $V_{CC}=3.0\,\text{V}$
- LVCMOS Compatible
- 24 mA Output Sink Capability
- Near Zero Static Supply Current Substantially Reduces System Power Requirements
- Chip Complexity: FET = 72; Equivalent Gate = 18
- Pb-Free Package is Available

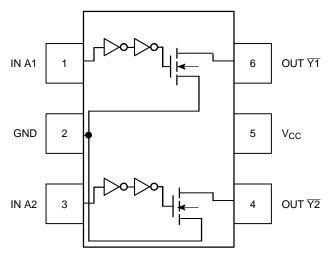


Figure 1. Pinout (Top View)

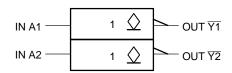


Figure 2. Logic Symbol



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MARKING DIAGRAMS



SC-88 DF SUFFIX CASE 419B





TSOP-6 DT SUFFIX CASE 318G



Pin 1 d = Date Code

PIN ASSIGNMENT

1	IN A1
2	GND
3	IN A2
4	OUT Y2
5	Vcc
6	OUT Y1

FUNCTION TABLE

A Input	▼ Output
L	Z
Н	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	Characteristics	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V
VI	DC Input Voltage	$-0.5 \le V_1 \le +7.0$	V
Vo	DC Output Voltage Output in Z or LOW State (Note 1)	$-0.5 \le V_O \le 7.0$	V
I _{IK}	DC Input Diode Current $V_I < GND$	-50	mA
I _{OK}	DC Output Diode Current V _O < GND	-50	mA
I _O	DC Output Sink Current	±50	mA
I _{CC}	DC Supply Current Per Supply Pin	±100	mA
I _{GND}	DC Ground Current Per Ground Pin	±100	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C
P _D	Power Dissipation in Still Air SC-88, TSOP-6	200	mW
θ_{JA}	Thermal resistance SC-88, TSOP-6	333	°C/W
TL	Lead temperature, 1 mm from case for 10 s	260	°C
TJ	Junction temperature under bias	+150	°C
V _{ESD}	ESD Withstand Voltage Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 N/A	V
I _{Latch-Up}	Latch-Up Performance Above V _{CC} and Below GND at 85°C (Note 5)	±500	mA

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur araimum rating must be affected.

1. Io absolute maximum rating must be observed.

- Tested to EIA/JESD22-A114-A
 Tested to EIA/JESD22-A115-A
- Tested to JESD22-C101-A
 Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	Supply Voltage	Operating Data Retention Only	1.65 1.5	5.5 5.5	V
VI	Input Voltage		0	5.5	V
Vo	Output Voltage	(Z or LOW State)	0	5.5	V
T _A	Operating Free-Air Temperature		– 55	+125	°C
Δt/ΔV	Input Transition Rise or Fall Rate	$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$ $V_{CC} = 3.0 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0 0 0	20 10 5	ns/V

DC ELECTRICAL CHARACTERISTICS

			Vcc	T _A = 25°C			-40°C ≤ 1	Γ _A ≤ 85°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Unit
V_{IH}	High-Level Input Voltage		1.65 2.3 to 5.5	0.75 V _{CC} 0.70 V _{CC}			0.75 V _{CC} 0.70 V _{CC}		V
V _{IL}	Low-Level Input Voltage		1.65 2.3 to 5.5			0.25 V _{CC} 0.30 V _{CC}		0.25 V _{CC} 0.30 V _{CC}	V
I _{LKG}	Z-State Output Leakage Current	$V_{IN} = V_{IL}$ $V_{OUT} = V_{CC}$ or GND	1.65 to 5.5			±5.0		±10.0	μΑ
V _{OL}	Low-Level Output Voltage	I _{OL} = 100 μA	1.65 to 5.5		0.0	0.1		0.1	V
	$V_{IN} = V_{IH}$	I _{OL} = 3 mA	1.65		0.08	0.24			
		I _{OL} = 8 mA	2.3		0.22	0.3		0.3	
		I _{OL} = 12 mA	2.7		0.22	0.4		0.4	
		I _{OL} = 16 mA	3.0		0.28	0.4		0.4	
		I _{OL} = 24 mA	3.0		0.38	0.55		0.55	
		I _{OL} = 32 mA	4.5		0.42	0.55		0.55	
I _{IN}	Input Leakage Current	V _{IN} or V _{OUT} = V _{CC} or GND	0 to 5.5			±0.1		±1.0	μΑ
I _{OFF}	Power Off-Output Leakage Current	V _{OUT} = 5.5 V	0			1		10	μΑ
Icc	Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			1		10	μΑ

AC ELECTRICAL CHARACTERISTICS $t_R=t_F=2.5$ ns; $C_L=50$ pF; $R_L=500~\Omega$

				T _A = 25°C		C	-40°C ≤ 1	T _A ≤ 85°C	
Symbol	Parameter	Condition	V _{CC} (V)	Min	Тур	Max	Min	Max	Unit
t _{PZL}	Propagation Delay	$R_{L} = R_1 = 5000 \Omega, C_L = 15 pF$	1.8 ± 0.15	2.0	5.7	10.5	2.0	11.0	ns
	(Figure 3 and 4)	$R_{L} = R_1 = 500 \Omega, C_L = 50 pF$	2.5 ± 0.20	0.8	3.0	3.6	0.8	4.1	
		$R_{L} = R_1 = 500 \Omega, C_L = 50 pF$	3.3 ± 0.30	0.8	2.4	3.2	0.8	3.7	
		$R_{L} = R_1 = 500 \Omega, C_L = 50 pF$	5.0 ± 0.50	0.5	2.4	3.0	0.5	3.5	
t _{PLZ}	Propagation Delay	$R_{L} = R_1 = 5000 \Omega, C_L = 15 pF$	1.8 ± 0.15	2.0	5.7	10.5	2.0	11.0	ns
	(Figure 3 and 4)	$R_{L} = R_1 = 500 \Omega, C_L = 50 pF$	2.5 ± 0.20	0.8	3.0	3.6	0.8	4.1	
		$R_{L} = R_1 = 500 \Omega, C_L = 50 pF$	3.3 ± 0.30	0.8	2.1	3.2	0.8	3.7	
		$R_{L=} R_{1}=500 \Omega, C_{L}=50 pF$	5.0 ± 0.50	0.5	1.2	3.0	0.5	3.5	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	V_{CC} = 5.5 V, V_{I} = 0 V or V_{CC}	2.5	pF
C _{OUT}	Output Capacitance	V_{CC} = 5.5 V, V_{I} = 0 V or V_{CC}	4	pF
C _{PD}	Power Dissipation Capacitance (Note 6)	10 MHz, $V_{CC} = 5.5 \text{ V}$, $V_{I} = 0 \text{ V}$ or V_{CC}	4	pF

^{6.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

DC ELECTRICAL CHARACTERISTICS

			Vcc	T _A = 25°C			-55°C ≤ T	A ≤ 125°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Unit
V_{IH}	High-Level Input Voltage		1.65 2.3 to 5.5	0.75 V _{CC} 0.70 V _{CC}			0.75 V _{CC} 0.70 V _{CC}		V
V _{IL}	Low-Level Input Voltage		1.65 2.3 to 5.5			0.25 V _{CC} 0.30 V _{CC}		0.25 V _{CC} 0.30 V _{CC}	V
I _{LKG}	Z-State Output Leakage Current	$V_{IN} = V_{IL}$ $V_{OUT} = V_{CC}$ or GND	1.65 to 5.5			±5.0		±10.0	μΑ
V _{OL}	Low-Level Output Voltage	I _{OL} = 100 μA	1.65 to 5.5		0.0	0.1		0.1	V
	$V_{IN} = V_{IH}$	I _{OL} = 3 mA	1.65		0.08	0.24			
		I _{OL} = 8 mA	2.3		0.22	0.3		0.35	
		I _{OL} = 12 mA	2.7		0.22	0.4		0.45	
		I _{OL} = 16 mA	3.0		0.28	0.4		0.5	
		I _{OL} = 24 mA	3.0		0.38	0.55		0.65	
		I _{OL} = 32 mA	4.5		0.42	0.55		0.65	
I _{IN}	Input Leakage Current	V _{IN} or V _{OUT} = V _{CC} or GND	0 to 5.5			±0.1		±1.0	μΑ
I _{OFF}	Power Off-Output Leakage Current	V _{OUT} = 5.5 V	0			1		10	μΑ
Icc	Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			1		10	μΑ

AC ELECTRICAL CHARACTERISTICS $t_R=t_F=2.5$ ns; $C_L=50$ pF; $R_L=500~\Omega$

				T _A = 25°C		-55 °C ≤ T_A ≤ 125°C			
Symbol	Parameter	Condition	V _{CC} (V)	Min	Тур	Max	Min	Max	Unit
t _{PZL}	Propagation Delay	$R_{L} = R_1 = 5000 \Omega, C_L = 15 pF$	1.8 ± 0.15	2.0	5.7	10.5	2.0	11.0	ns
	(Figure 3 and 4)	$R_{L=} R_{1}=500 \Omega, C_{L}=50 pF$	2.5 ± 0.20	0.8	3.0	3.6	0.8	4.1	
		$R_{L=} R_{1}=500 \Omega, C_{L}=50 pF$	3.3 ± 0.30	0.8	2.4	3.2	0.8	3.7	
		$R_{L} = R_1 = 500 \Omega, C_L = 50 pF$	5.0 ± 0.50	0.5	2.4	3.0	0.5	3.5	
t _{PLZ}	Propagation Delay	$R_{L} = R_1 = 5000 \Omega, C_L = 15 pF$	1.8 ± 0.15	2.0	5.7	10.5	2.0	11.0	ns
	(Figure 3 and 4)	$R_{L} = R_1 = 500 \Omega, C_L = 50 pF$	2.5 ± 0.20	0.8	3.8	4.5	0.8	5.0	
		$R_{L=} R_{1}=500 \Omega, C_{L}=50 pF$	3.3 ± 0.30	0.8	2.9	3.2	0.8	3.7	
		$R_{L=} R_{1}=500 \Omega, C_{L}=50 pF$	5.0 ± 0.50	0.5	1.2	3.0	0.5	3.5	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	V_{CC} = 5.5 V, V_{I} = 0 V or V_{CC}	2.5	pF
C _{OUT}	Output Capacitance	V_{CC} = 5.5 V, V_{I} = 0 V or V_{CC}	4	pF
C _{PD}	Power Dissipation Capacitance (Note 6)	10 MHz, $V_{CC} = 5.5 \text{ V}$, $V_{I} = 0 \text{ V}$ or V_{CC}	4	pF

^{7.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

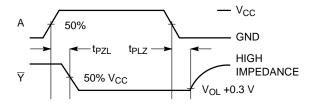
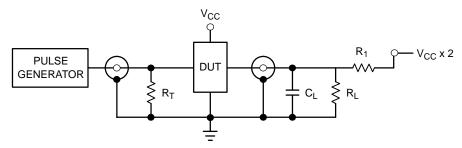


Figure 3. Switching Waveforms



 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 4. Test Circuit

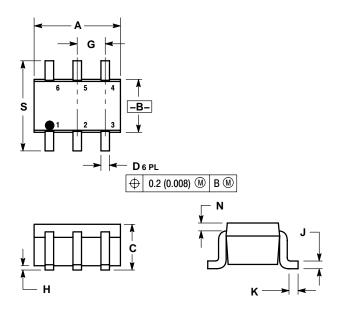
ORDERING INFORMATION

Device	Logic Circuit Indicator	No. of Gates per Package	Temp Range Identifier	Technology	Device Function	Package Suffix	Tape & Reel Suffix _†	Package	Shipping [†]
NL27WZ06DFT2	NL	2	7	WZ	06	DF	T2	SC-88	3000 / Tape & Reel
NL27WZ06DFT2G	NL	2	7	WZ	06	DF	T2	SC-88 (Pb-Free)	3000 / Tape & Reel
NL27WZ06DTT1	NL	2	7	WZ	06	DT	T1	TSOP-6	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

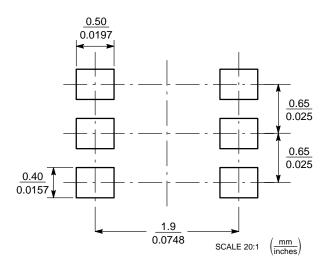
SC-88/SC70-6/SOT-363 CASE 419B-02 ISSUE U



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
C	0.031	0.043	0.80	1.10	
D	0.004	0.012	0.10	0.30	
G	0.026	BSC	0.65 BSC		
Η		0.004		0.10	
J	0.004	0.010	0.10	0.25	
K	0.004	0.012	0.10	0.30	
N	0.008	REF	0.20 REF		
S	0.079	0.087	2.00	2.20	

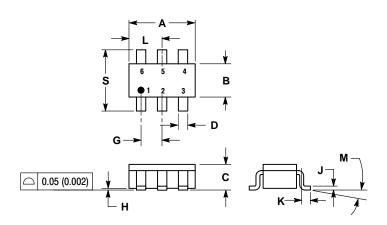
SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

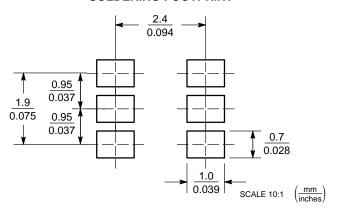
TSOP-6 CASE 318G-02 ISSUE L



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.1142	0.1220
В	1.30	1.70	0.0512	0.0669
С	0.90	1.10	0.0354	0.0433
D	0.25	0.50	0.0098	0.0197
G	0.85	1.05	0.0335	0.0413
Н	0.013	0.100	0.0005	0.0040
J	0.10	0.26	0.0040	0.0102
K	0.20	0.60	0.0079	0.0236
L	1.25	1.55	0.0493	0.0610
М	0 °	10 °	0 °	10°
S	2.50	3.00	0.0985	0.1181

SOLDERING FOOTPRINT



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